

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	50mΩ@-4.5V	-5A
	70mΩ@-2.5V	

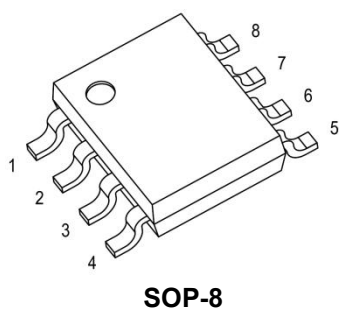
Feature

- $V_{DS} = -20V, I_D = -5A$
 $R_{DS(ON)} < 90m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

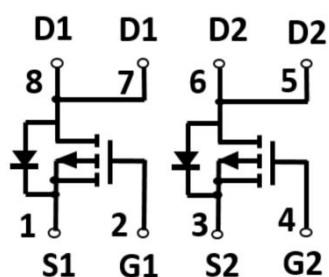
Application

- PWM applications
- Load switch
- Power management

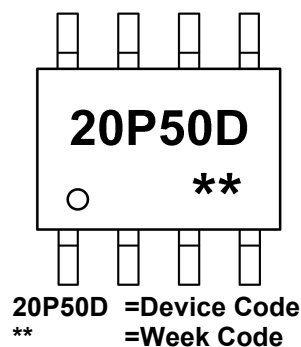
Package



Circuit diagram



Marking



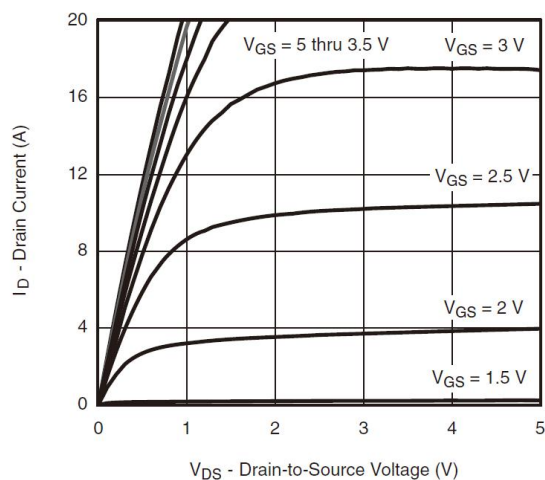
**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-5	A
Drain Current-Pulsed	I_{DM}	-20	A
Power Dissipation	P_D	3.1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	52	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

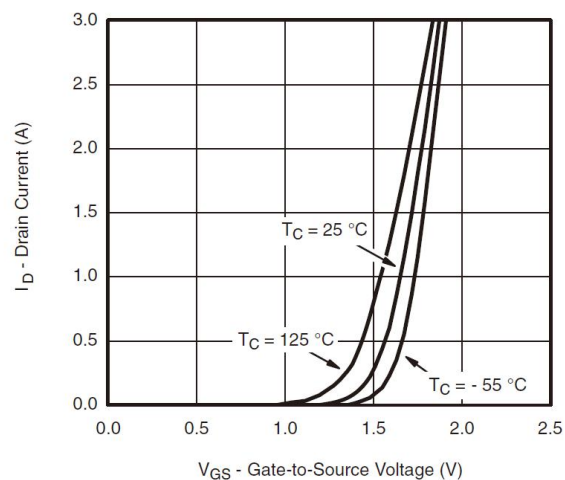
Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250μA	-0.5	-0.7	-1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -4A		50	60	mΩ
		V _{GS} = -2.5V, I _D = -2A		70	90	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V,f=1MHz		405		pF
Output Capacitance	C _{oss}			75		
Reverse Transfer Capacitance	C _{rss}			55		
Total Gate Charge	Q _g	V _{DS} =-10V,V _{GS} =-2.5V,I _D =-3A		3.3	12	nC
Gate-Source Charge	Q _{gs}			0.7		
Gate-Drain Charge	Q _{gd}			1.3		
Turn-on delay time	t _{d(on)}	V _{DD} =-10V,V _{GEN} =-4.5V,I _D =-1A R _L =10Ω,R _{GEN} =1Ω		11		ns
Turn-on rise time	t _r			35		
Turn-off delay time	t _{d(off)}			30		
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =-1A		-0.7	-1.3	V

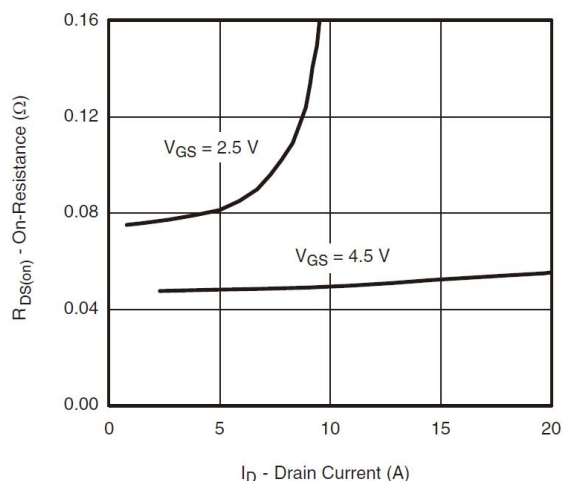
Typical Characteristics



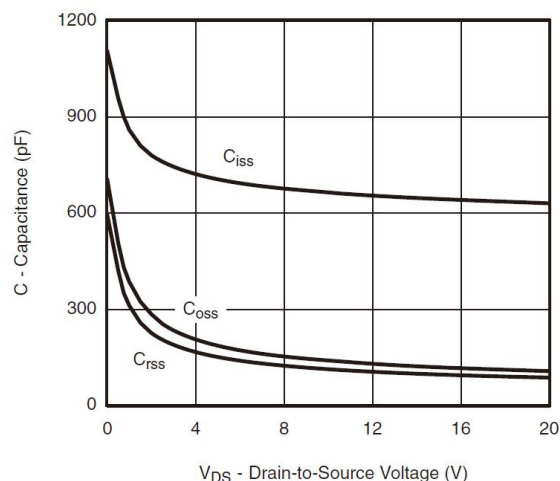
Output Characteristics



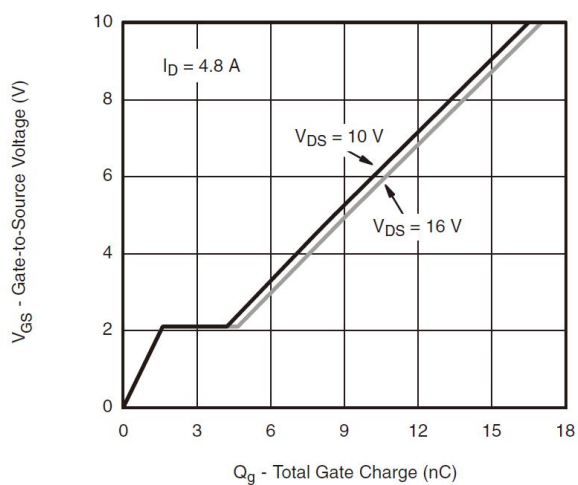
Transfer Characteristics



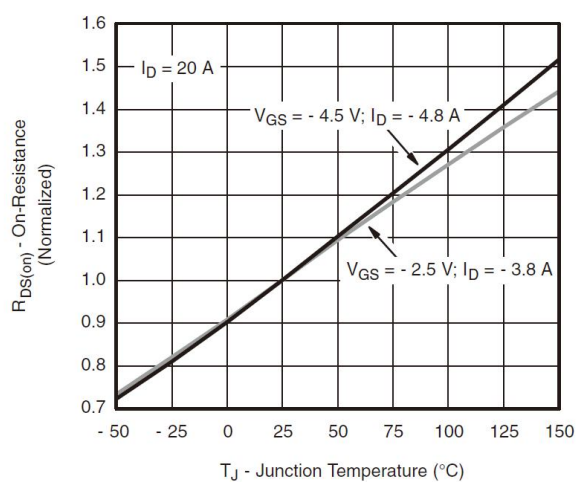
On-Resistance vs. Drain Current and Gate Voltage



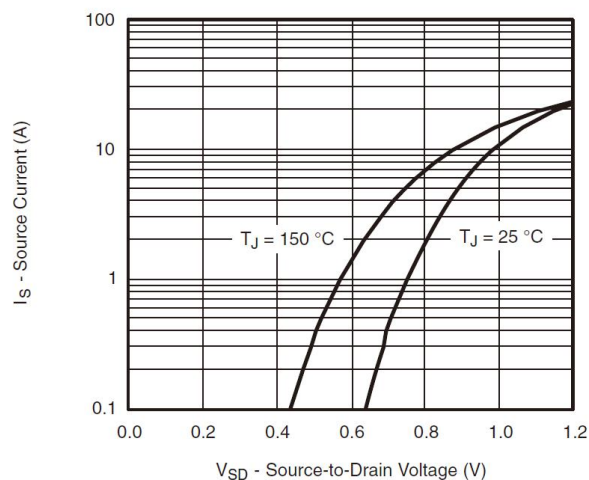
Capacitance



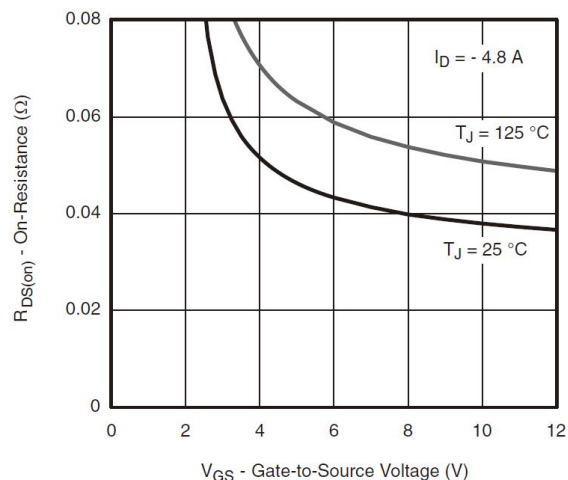
Gate Charge



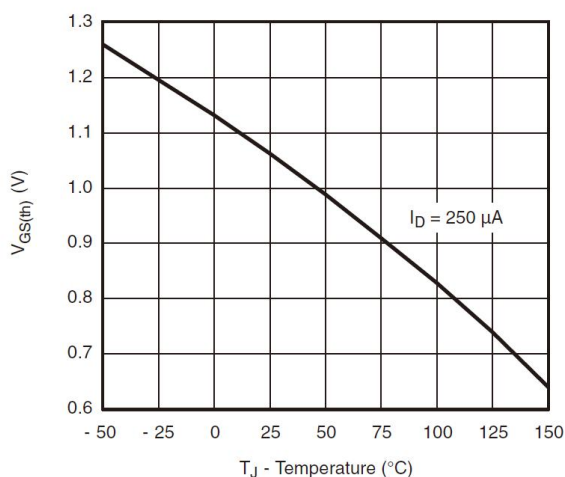
On-Resistance vs. Junction Temperature



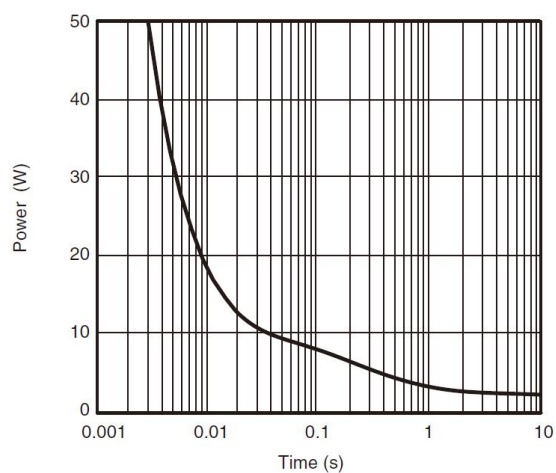
Source-Drain Diode Forward Voltage



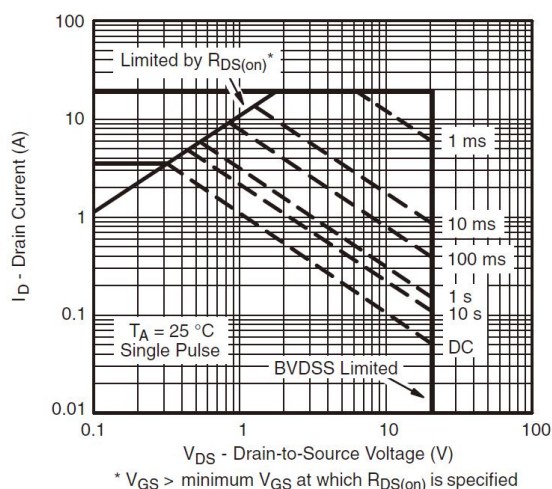
On-Resistance vs. Gate-to-Source Voltage



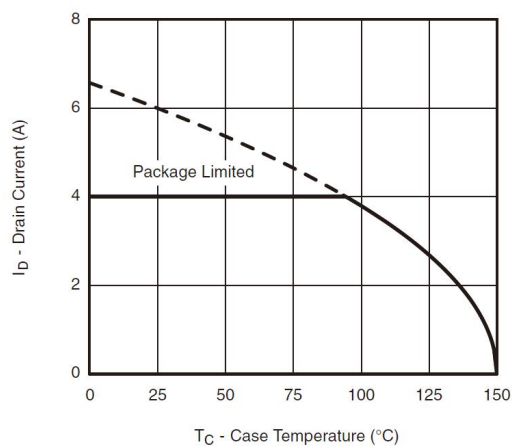
Threshold Voltage



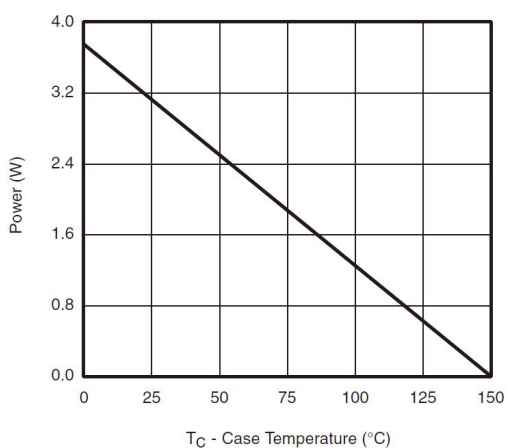
Single Pulse Power, Junction-to-Ambient



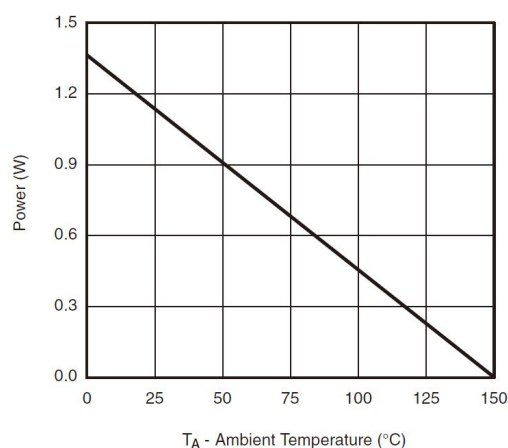
Safe Operating Area, Junction-to-Ambient



Current Derating ^a



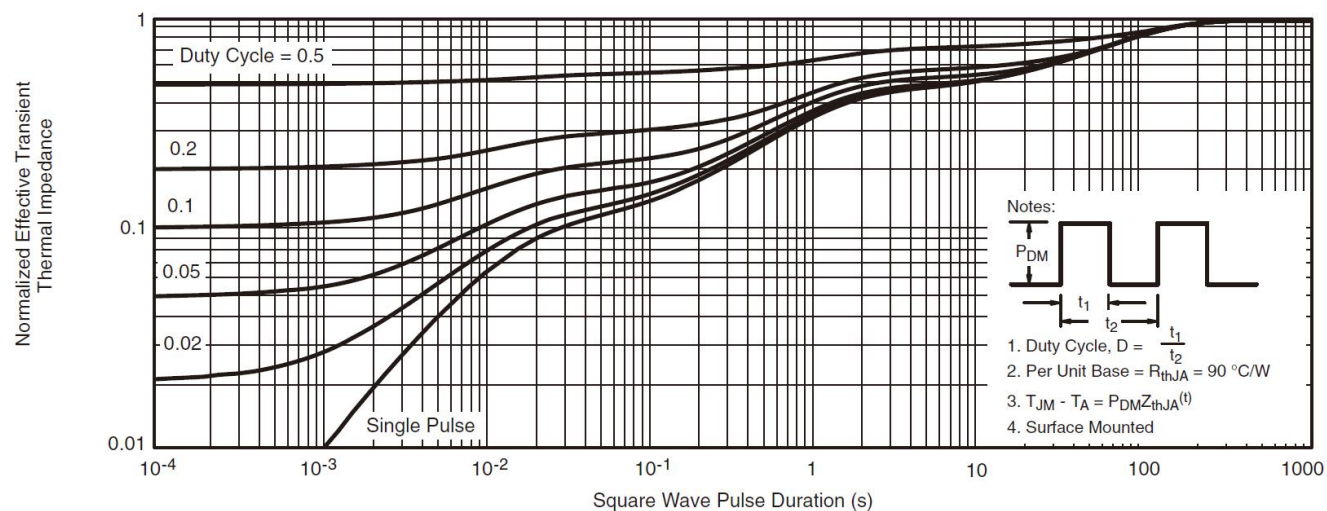
Power Derating, Junction-to-Foot



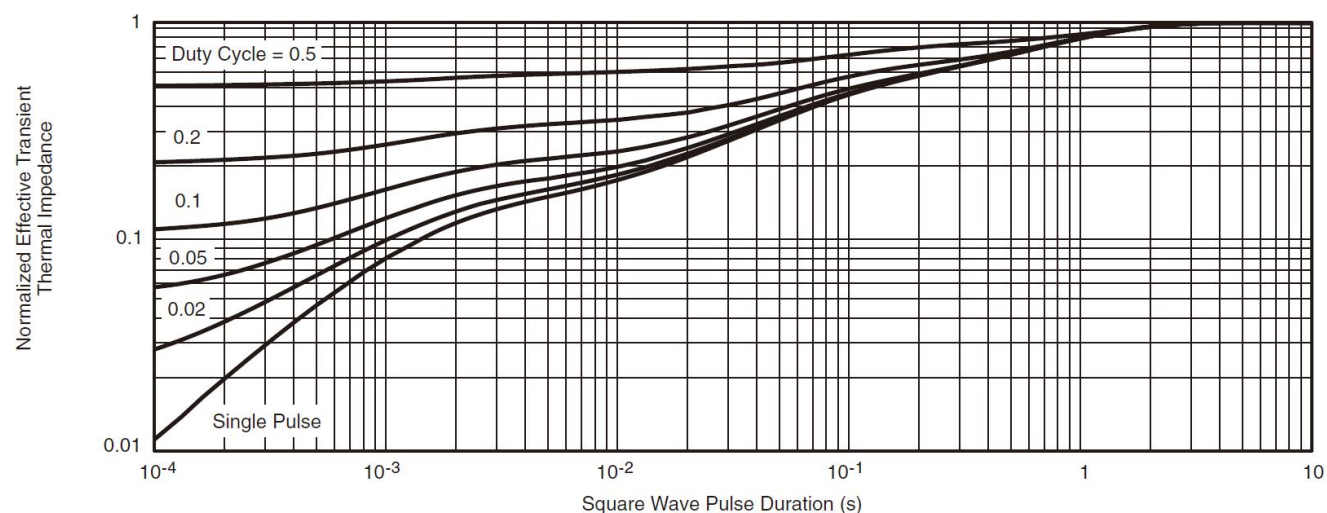
Power Derating, Junction-to-Ambient

Note

- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



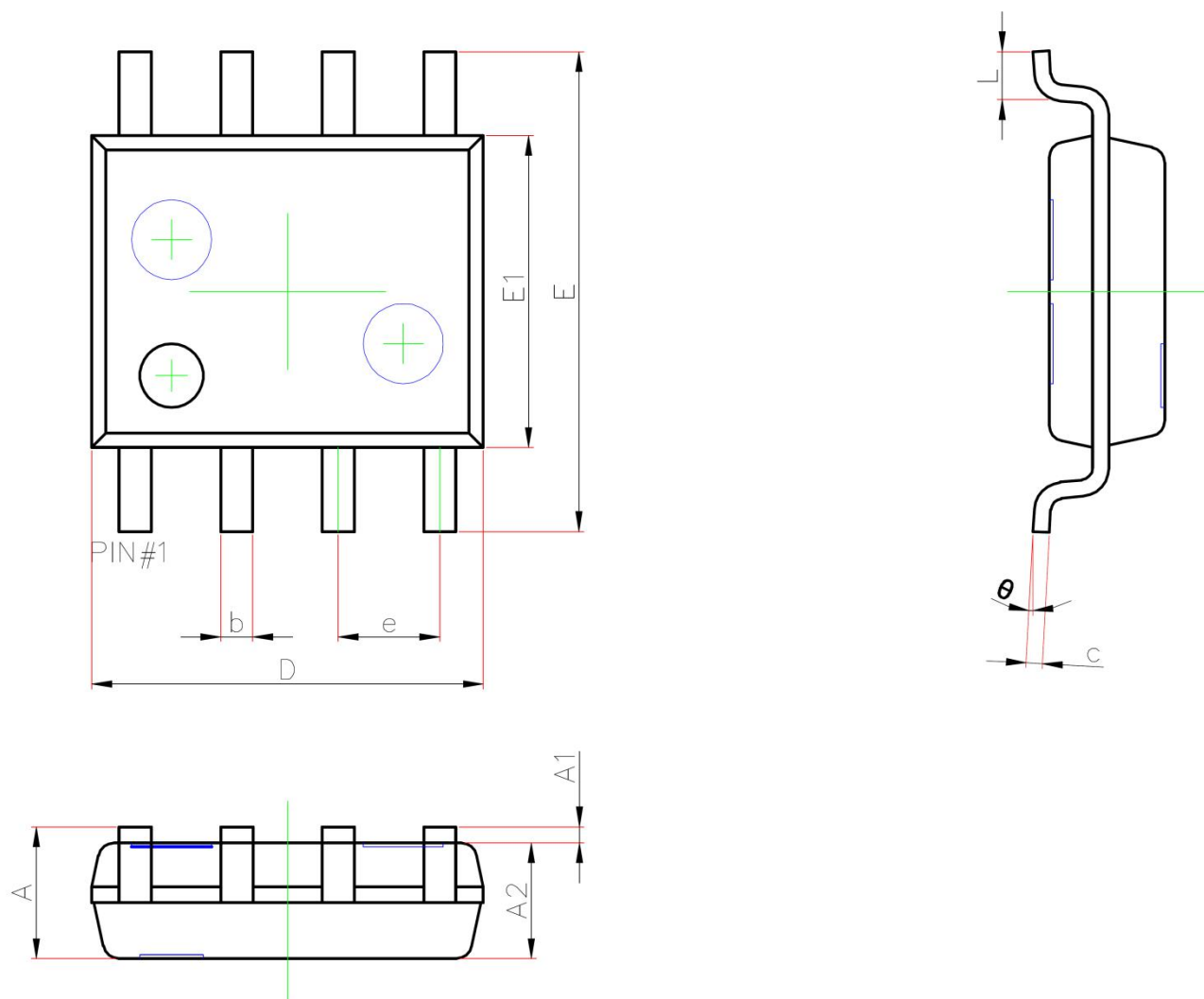
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot



SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°